

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	68059	(a-si or asi or ((amorphous or alpha) near2 (si or silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:39
2	BRS	2136	((a-si or asi or ((amorphous or alpha) near2 (si or silicon)))) near8 (PVD or "physical vapor deposition" or sputter\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 10:58
3	BRS	74999	(aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 10:58
4	BRS	11723 5	polysilicon or poly-silicon or polysi or poly-si or (poly near2 (si or silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 10:58
5	BRS	11790 75	crystal\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 10:59
6	BRS	474	((aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6) near8 (polysilicon or poly-silicon or polysi or poly-si or (poly near2 (si or silicon))) near8 crystal\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 10:59
7	BRS	360	((aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6) near8 crystal\$6 near8 (polysilicon or poly-silicon or polysi or poly-si or (poly near2 (si or silicon))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 10:59

Type	Hits	Search Text	DBs	Time Stamp
8	BRS 35	((a-si or asi or ((amorphous or alpha) near2 (si or silicon)))) near8 (PVD or "physical vapor deposition" or sputter\$6)) and (((aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6) near8 crystal\$6 near8 (polysilicon or poly-silicon or polysi or poly-si or (poly near2 (si or silicon))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 10:59
9	BRS 59622	(TFT or "thin film transistor" or T-F-T)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:00
10	BRS 16177	(metal adj induc\$4 adj crystal\$6) or MIC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:00
11	BRS 861	((aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6) same crystal\$6 same (polysilicon or poly-silicon or polysi or poly-si or (poly near2 (si or silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:01
12	BRS 49	((a-si or asi or ((amorphous or alpha) near2 (si or silicon)))) near8 (PVD or "physical vapor deposition" or sputter\$6)) and (((aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6) same crystal\$6 same (polysilicon or poly-silicon or polysi or poly-si or (poly near2 (si or silicon))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:01

	Type	Hits	Search Text	DBs	Time Stamp
13	BRS	28	(((a-si or asi or ((amorphous or alpha) near2 (si or silicon)))) near8 (PVD or "physical vapor deposition" or sputter\$6)) and (((aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6) near8 crystal\$6 near8 (polysilicon or poly-silicon or polysi or poly-si or (poly near2 (si or silicon)))) and ((TFT or "thin film transistor" or T-F-T))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:01
14	BRS	3	(((a-si or asi or ((amorphous or alpha) near2 (si or silicon)))) near8 (PVD or "physical vapor deposition" or sputter\$6)) and (((aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6) near8 crystal\$6 near8 (polysilicon or poly-silicon or polysi or poly-si or (poly near2 (si or silicon)))) and ((TFT or "thin film transistor" or T-F-T)) and ((metal adj induc\$4 adj crystal\$6) or MIC)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:01
15	IS&R	814	(438/166).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:01
16	IS&R	745	(438/482).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:31
17	BRS	7054	SPC or (suppress\$6 near2 (partial adj solid adj phase adj crystalliz\$6))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:39

	Type	Hits	Search Text	DBs	Time Stamp
18	BRS	208	(SPC or (suppress\$6 near2 (partial adj solid adj phase adj crystalliz\$6))) same ((a-si or asi or ((amorphous or alpha) near2 (si or silicon))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:39
19	BRS	80	((SPC or (suppress\$6 near2 (partial adj solid adj phase adj crystalliz\$6))) same ((a-si or asi or ((amorphous or alpha) near2 (si or silicon)))) and (@ad<20001025)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:44
20	BRS	34	((SPC or (suppress\$6 near2 (partial adj solid adj phase adj crystalliz\$6))) same ((a-si or asi or ((amorphous or alpha) near2 (si or silicon)))) and (@ad<20001025)) and ((aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:44

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&R	L1	463	(438/486).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/17 14:32
2	IS&R	L3	120	(438/150).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/17 14:59